We claim:

1	1.	An acoustic transducer comprising:
2		a substrate having a topside and a backside;
3		a microfabricated acoustic transducer formed on the topside of the substrate; and
4		a damping material disposed on the backside of the substrate, the damping
5	material suppr	essing substrate acoustic modes.
1	2.	An apparatus according to claim 1 wherein the damping material has an acoustic
2	impedance tha	t is similar to the acoustic impedance of the substrate and is lossy.
1	3	An apparatus according to claim 1 further including electronic circuits formed in
2	the substrate.	
1	4.	An apparatus according to claim 3 wherein the electronics circuits are in between
2		the damping material.
4.	the sonsor and	
1	5.	An apparatus according to claim 1 wherein the substrate is a wafer.
1	6.	An apparatus according to claim 1 wherein the damping material suppresses a
2	longitudinal ri	inging mode.
1	7.	An apparatus according to claim 1 wherein the damping material suppresses a
1		
2	lamb wave rin	iging mode.
1	8.	An apparatus according to claim 1 wherein the microfabricated acoustic
2	transducer op	erates at frequencies above 20 kHz.
1	9.	An acoustic transducer comprising:
2	. *	a substrate having a topside and a backside, the substrate having a thickness such
3	that resonant	modes of the substrate are outside a frequency band of interest; and
4		a microfabricated acoustic transducer formed on the topside of the substrate.

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1	10.	An apparatus according to claim 9 further including:	
2		a damping material disposed on the backside of the substrate, the damping	
3	material supp	ressing substrate acoustic modes.	
.1	11.	An apparatus according to claim 10 wherein the damping material suppresses	
2	lamb wave m	odes.	
	10	the demains material has an acquetic	
1	12.	An apparatus according to claim 10 wherein the damping material has an acoustic	
2	impedance th	at is similar to the acoustic impedance of the substrate and is lossy.	
1	13.	An apparatus according to claim 12 further including electronic circuits formed in	
2	the substrate.		
1	14.	An apparatus according to claim 13 wherein the electronics circuits are in	
5.12	between the sensor and the damping material.		
: i 1	15.	An apparatus according to claim 9 further including electronic circuits formed in	
2	the substrate	•	
5.1			
1	16.	An apparatus according to claim 9 wherein the substrate is a wafer.	
in L	17.	An apparatus according to claim 9 wherein the microfabricated acoustic	
2	transducer of	perates at frequencies above 20 kHz.	
1	18.	An apparatus according to claim 9 wherein the damping material suppresses	
2	stonely wave	e modes.	
1	19.	A method for suppressing acoustic modes, the method comprising:	
2	17.	providing a substrate having a topside and a backside;	
		forming a microfabricated acoustic transducer on the topside of the substrate; and	
3		_	
4	_	placing a damping material on the backside of the substrate, the damping material	
5	suppressing	substrate acoustic modes.	

1	20.	The method of claim 19 wherein the damping material has an acoustic impedance
2	that is similar	to the acoustic impedance of the substrate and is lossy.
1	21.	The method of claim 20 further comprising forming electronic circuits in the
2	substrate.	
* =		
1	22.	The method of claim 21 wherein the electronics circuits are in between the sensor
2	and the dampi	ing material.
1	23.	The method of claim 19 wherein the substrate is a wafer.
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1	24.	The method of claim 19 wherein the damping material suppresses a longitudinal
2	ringing mode.	
4	25	The method of claim 19 wherein the damping material suppresses a lamb wave
1	25.	
2	ringing mode	•
1	26.	The method of claim 19 further comprising operating the microfabricated acoustic
2		frequencies above 20 kHz.
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1	27.	A method for suppressing acoustic modes, the method comprising:
2		providing a substrate having a topside and a backside, the substrate having a
3,	thickness such that resonant modes of the substrate are outside a frequency band of interest; and	
4		forming a microfabricated acoustic transducer on the topside of the substrate.
1	28.	An apparatus according to claim 27 further including:
2		a damping material disposed on the backside of the substrate, the damping
3	material supp	oressing substrate acoustic modes.
1	29.	The method of claim 28 wherein the damping material suppresses lamb wave
2	modes.	

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1	30.	The method of claim 28 wherein the damping material has an acoustic impedance	
2	that is similar	to the acoustic impedance of the substrate and is lossy.	
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1	31.	The method of claim 30 further comprising forming electronic circuits in the	
2	substrate.		
1	32.	The method of claim 31 wherein the electronics circuits are in between the sensor	
2	and the damping material.		
1	33.	The method of claim 27 further comprising forming electronic circuits in the	
2	substrate.	•	
1	34.	The method of claim 27 wherein the substrate is a wafer.	
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1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	35.	The method of claim 27 further comprising operating the microfabricated acoustic	
2	transducer at frequencies above 20 kHz.		
27.27.27.27.27.27.27.27.27.27.27.27.27.2			
1	36.	The method of claim 27 wherein the damping material suppresses stonely wave	
2	modes.		
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